Attorney Docket No. 5308-279 PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re: Sei-Hyung Ryu
Serial No.: To Be Assigned
Filed: Concurrently Herewith
For: VERTICAL JFET LIMITED SILICON CARBIDE POWER METAL-OXIDE SEMICONDUCTOR FIELD EFFECT TRANSISTORS AND METHODS OF FABRICATING VERTICAL JFET LIMITED SILICON CARBIDE METAL-OXIDE SEMICONDUCTOR FIELD EFFECT TRANSISTORS

Date: October 30, 2003

Mail Stop Patent Application
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. § 1.97(b)

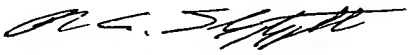
Sir:

Attached is a list of documents on Form PTO-1449, together with a copy of any listed foreign patent document and/or non-patent literature. A copy of any listed U.S. patent and/or U.S. patent application publication is not provided herewith in accordance with the waiver by the U.S. Patent and Trademark Office of requirements under 37 C.F.R. § 1.98(a)(2)(i) for all U.S. national patent applications filed after June 30, 2003 and for all international applications that have entered the national stage under 35 USC § 371 after June 30, 2003.

It is requested that these documents be considered by the Examiner and officially made of record in accordance with the provisions of 37 C.F.R. § 1.56 and Section 609 of the MPEP.

No fee is believed due. However, the Commissioner is hereby authorized to charge any deficiency or credit any overpayment to Deposit Account No. 50-0220.

Respectfully submitted,



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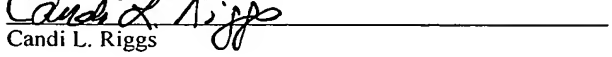

Candi L. Riggs

FORM PTO-1449 U.S. Department of Commerce Patent and Trademark Office LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary)	Attorney Docket Number: 5308-279	Serial No.: To Be Assigned
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U. S. PATENT DOCUMENTS

Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
	1	6,593,620	7/15/03	Hshieh et al.	257	335	
	2	6,455,892	9/02	Okuno	257	77	
	3	6,344,663 B1	2/5/02	Slater, Jr. et al.	257	77	
	4	6,297,172	10/2/01	Kashiwagi	438	773	
	5	6,246,076 B1	6/12/01	Lipkin et al.	257	77	
	6	6,239,463	5/29/01	Williams et al.	257	328	
	7	6,238,967 B1	5/29/01	Shiho et al.	438	244	
	8	6,221,700	4/24/01	Okuno et al.	438	151	
	9	6,211,035	4/01	Moise et al.	438	396	
	10	6,204,203	3/01	Narwanker et al.	438	785	
	11	6,190,973 B1	2/20/01	Berg et al.	438	275	
	12	6,165,822	12/26/00	Okuno et al.	438	142	
	13	6,136,728	10/24/00	Wang			
	14	6,117,735	9/12/00	Ueno	438	268	
	15	6,107,142	8/22/00	Suvorov et al.	438	285	
	16	6,100,169	8/8/00	Suvorov et al.	438	519	
	17	6,096,607	8/1/00	Ueno	438	522	
	18	6,063,698	5/16/00	Tseng et al.			
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	20	6,048,766	4/11/00	Gardner et al.			
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	22	6,025,608	2/15/00	Harris et al.	257	77	
	23	5,972,801	10/26/99	Lipkin et al.	438	770	
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	27	5,885,870A	3/99	Maiti et al.	438	261	

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	29	5,763,905	6/9/98	Harris	257	77	
	30	5,726,463	3/10/98	Brown et al.	257	77	
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	33	5,184,199	2/2/93	Fujii et al.	29	10	
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	39	2002/0072247	6/13/02	Lipkin et al.	438	767	
	40	2001/0055852	12/01	Moise et al.	438	396	

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		Document Number	Date	Country	Class	Subclass	Translation Yes | No
	41	0637069 A1/ B1	2/1/95	EPO			
	42	DE 10036208	2/14/02	Germany			Abstract
	43	DE 198 09 554	9/10/98	Germany			Abstract
	44	DE 19900171	12/26/00	Germany			Abstract
	45	JP 03157974	7/5/91	Japan			Abstract
	46	JP 08264766	10/11/96	Japan			Abstract
	47	JP 09205202	8/5/97	Japan			Abstract
	48	JP 11191559	7/13/99	Japan			Abstract
	49	JP 11238742	8/31/99	Japan			Abstract
	50	JP 11261061	9/24/99	Japan			Abstract
	51	JP 11266017	9/28/99	Japan			Abstract
	52	JP 11274487	10/8/99	Japan			Abstract
	53	JP 2000049167	2/18/00	Japan			Abstract
	54	JP 2000082812	3/21/00	Japan			Abstract

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	55	JP 2000106371	4/11/01	Japan			Abstract
	56	JP0200025246	9/14/00	Japan			Abstract
	57	WO 97/17730	5/15/97	PCT			
	58	WO 97/39485	10/23/97	PCT			

		59OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)
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	76	G.Y. Chung, C.C. Tin, J.R. Williams, K. McDonald, M. Di Ventra, S.T. Pantelides, L.C. Feldman, and R.A. Weller, "Effect of nitric oxide annealing on the interface trap densities near the band edges in the 4H polytype of silicon carbide," *Applied Physics Letters*, Vol. 76, No. 13, pp.1713-1715, March 2000.
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	80	J.B. Casady, A.K. Agarwal, L.B. Rowland, W.F. Valek, and C.D. Brandt, "900 V DMOS and 1100 V UMOS 4H-SiC Power FETs," *IEEE Device Research Conference*, Ft. Collins, CO June 23-25, 1997.
	81	J.N. Shenoy, J.A. Cooper and M.R. Meelock, "High-Voltage Double-Implanted Power MOSFETs in 6H-SiC," *IEEE Electron Device Letters*, Vol. 18, No. 3, pp.93-95, March 1997
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	90	M. K. Das, L.A. Lipkin, J.W. Palmour, G.Y. Chung, J.R. Williams, K. McDonald, and L.C. Feldman, "High Mobility 4H-SiC Inversion Mode MOSFETs Using Thermally Grown, NO Annealed SiO_2," *IEEE Device Research Conference*, Denver, CO June 19-21, 2000.
	91	M.A. Capano, S. Ryu, J.A. Cooper, Jr., M.R. Melloch, K. Rottner, S. Karlsson, N. Nordell, A. Powell, and D.E. Walker, Jr., "Surface Roughening in Ion Implanted 4H-Silicon Carbide," *Journal of Electronic Materials*, Vol. 28, No. 3, pp. 214-218, March 1999.
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